



STTH3L06

TURBO 2 ULTRAFast HIGH VOLTAGE RECTIFIER

MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	3 A
V_{RRM}	600 V
$I_R (max)$	100 μ A
$T_j (max)$	175 °C
$V_F (max)$	1.05 V
$trr (max)$	85 ns

FEATURES AND BENEFITS

- Ultrafast switching
- Low reverse recovery current
- Reduces switching & conduction losses
- Low thermal resistance

DESCRIPTION

The STTH3L06, which is using ST Turbo 2 600V technology, is specially suited as boost diode in discontinuous or critical mode power factor corrections.

The device is also intended for use as a free wheeling diode in power supplies and other power switching applications.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		600	V
$I_{F(RMS)}$	RMS forward current		20	A
$I_{F(AV)}$	Average forward current	$T_I = 100^\circ\text{C}$ $\delta = 0.5$	3	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10 \text{ ms}$ Sinusoidal	80	A
T_{stg}	Storage temperature range		- 65 + 175	°C
T_j	Maximum operating junction temperature		+ 175	°C

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THERMAL PARAMETERS

Symbol	Parameter		Maximum	Unit
$R_{th(j-l)}$	Junction to lead	L = 10 mm	20	°C/W
$R_{th(j-a)}$	Junction to ambient (note 1)	L = 10 mm	75	

Note 1: With recommended pad layout (see Fig 12)

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
I_R	Reverse leakage current	$V_R = 600V$	$T_j = 25^\circ C$			3	μA
			$T_j = 150^\circ C$		15	100	
V_F	Forward voltage drop	$I_F = 3 A$	$T_j = 25^\circ C$			1.3	V
			$T_j = 150^\circ C$		0.85	1.05	

To evaluate the maximum conduction losses use the following equation :
 $P = 0.89 \times I_{F(AV)} + 0.055 I_{F(RMS)}^2$

DYNAMIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
trr	Reverse recovery time	$I_F = 1 A$ $di_F/dt = - 50 A/\mu s$ $V_R = 30V$	$T_j = 25^\circ C$		60	85	ns
tfr	Forward recovery time	$I_F = 3 A$ $di_F/dt = 100 A/\mu s$ $V_{FR} = 1.1 \times V_{Fmax}$	$T_j = 25^\circ C$			100	ns
V_{FP}	Forward recovery time	$I_F = 3 A$ $di_F/dt = 100 A/\mu s$	$T_j = 25^\circ C$			7.5	V

Fig. 1: Conduction losses versus average current.

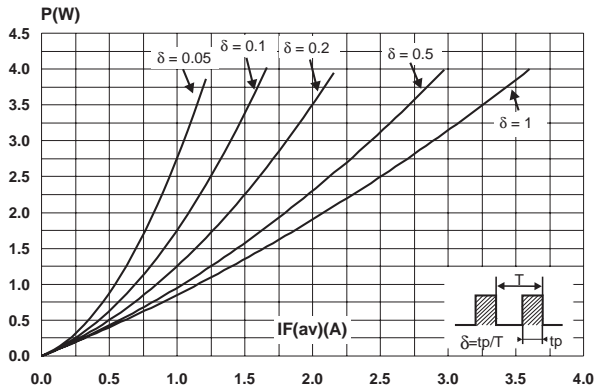


Fig. 2: Forward voltage drop versus forward current.

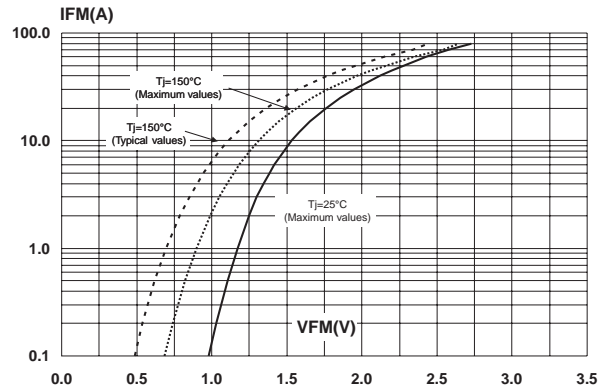


Fig. 3: Relative variation of thermal impedance junction ambient versus pulse duration (epoxy FR4, Leads = 10mm)

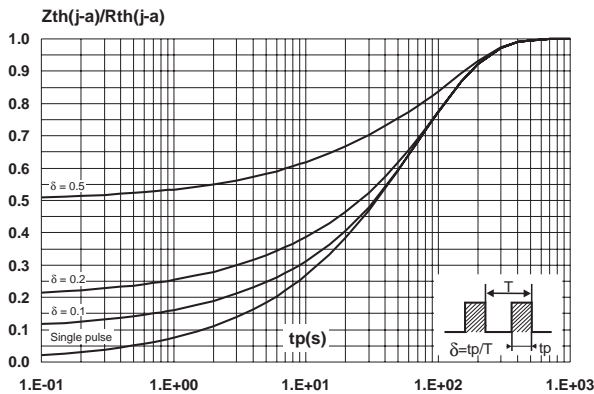


Fig. 4: Peak reverse recovery current versus dIF/dt (90% confidence).

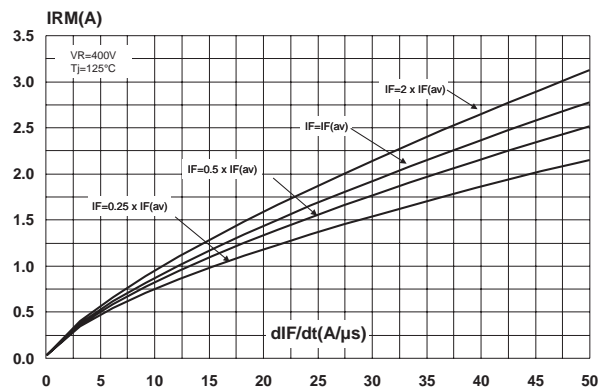


Fig. 5: Reverse recovery time versus dIF/dt (90% confidence).

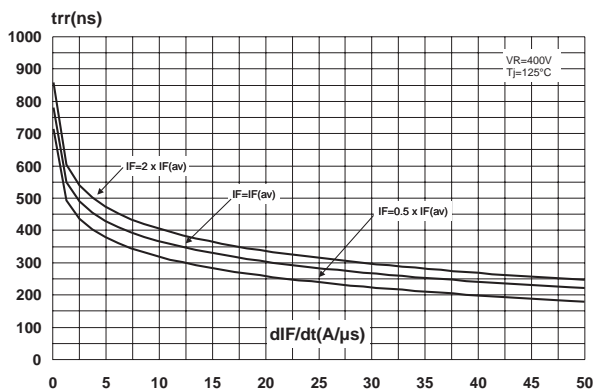


Fig. 6: Reverse recovery charges versus dIF/dt (90% confidence).

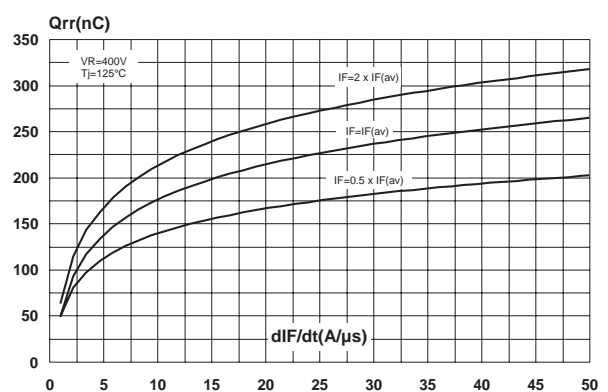


Fig. 7: Softness factor versus dI_F/dt (typical values).

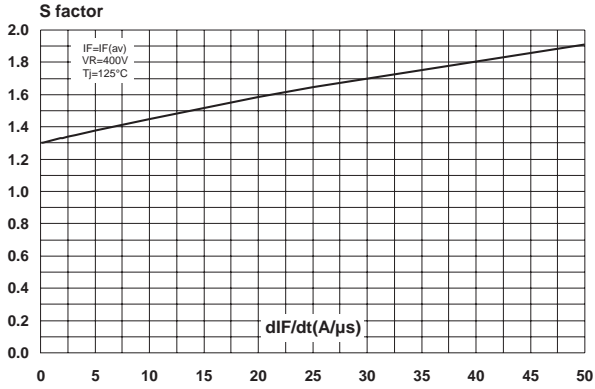


Fig. 8: Relative variations of dynamic parameters versus junction temperature.

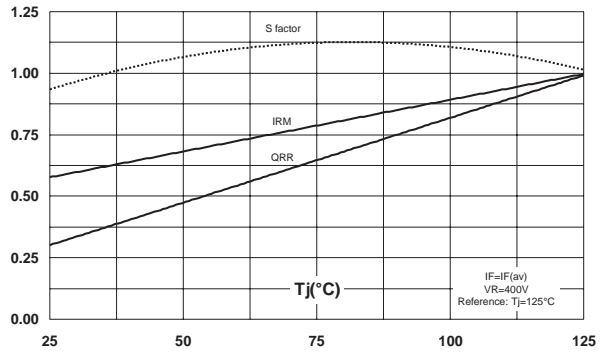


Fig. 9: Transient peak forward voltage versus dI_F/dt (90% confidence).

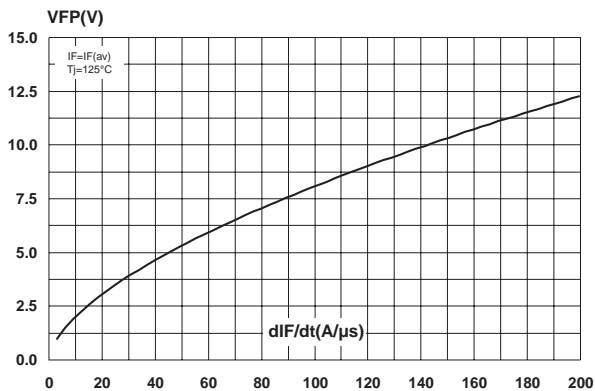


Fig. 10: Forward recovery time versus dI_F/dt (90% confidence).

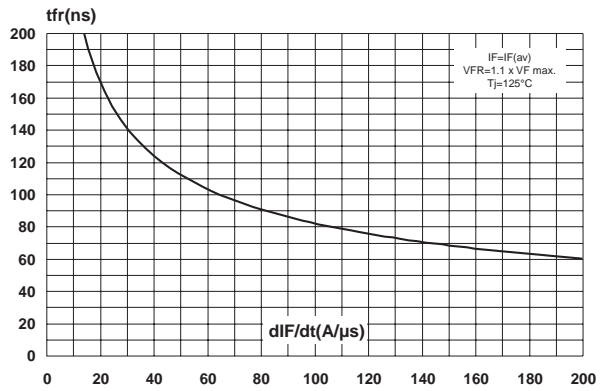


Fig. 11: Junction capacitance versus reverse voltage applied (typical values).

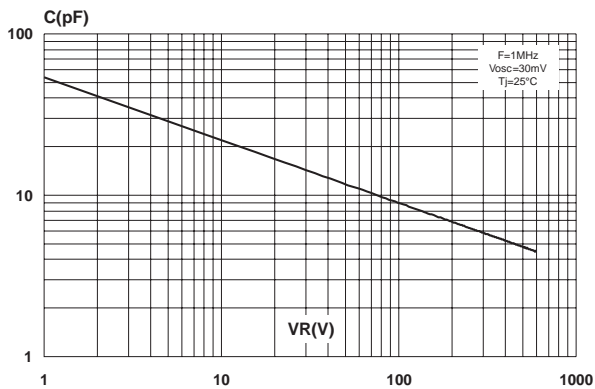
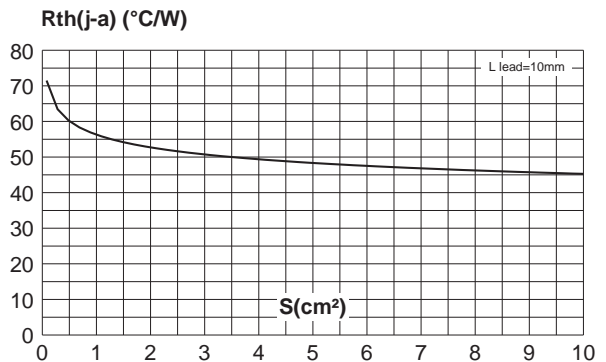
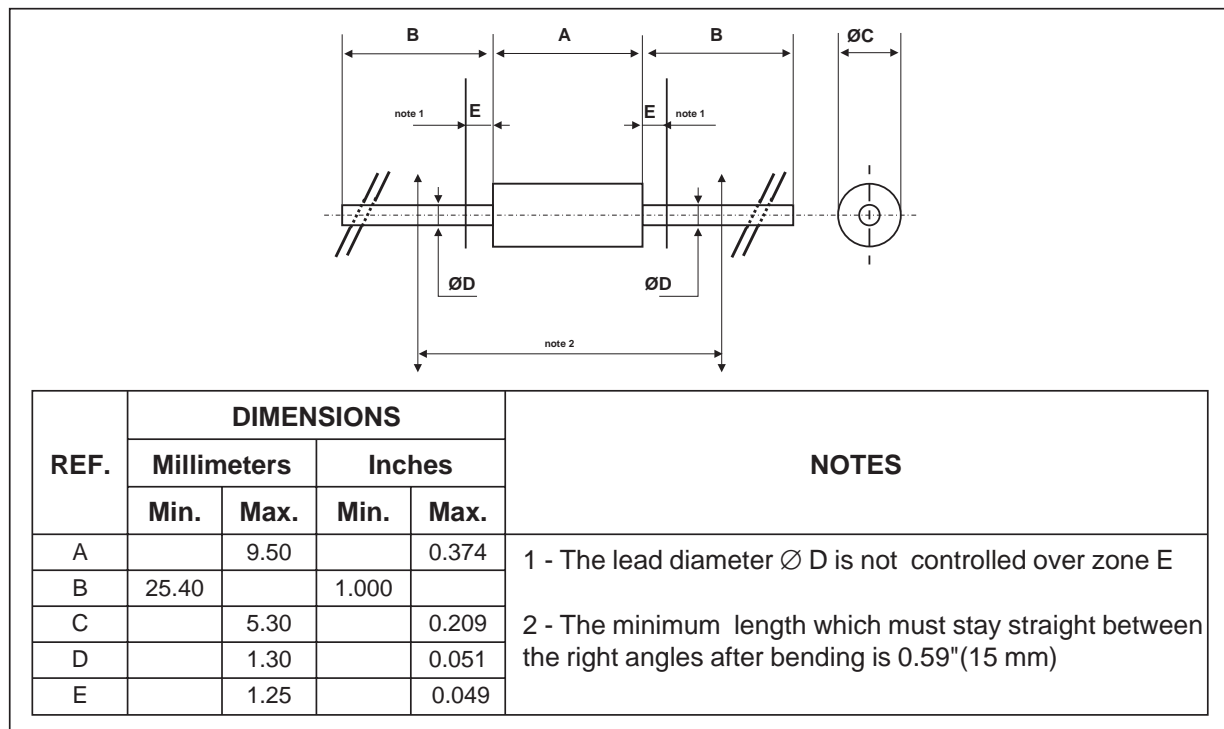


Fig. 12: Thermal resistance junction to ambient versus copper surface under each lead (Epoxy printed circuit board FR4, copper thickness: 35 μ m)



PACKAGE MECHANICAL DATA
 DO-201AD


Ordering code	Marking	Package	Weight	Base qty	Delivery mode
STTH3L06	STTH3L06	DO-201AD	1.12 g	600	Ammopack
STTH3L06RL	STTH3L06	DO-201AD	1.12 g	1900	Tape & reel

- Epoxy meets UL 94,V0
- Band indicated cathode
- Bending method: Application note AN1471

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